

HiPerFET™

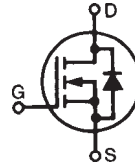
Power MOSFETs

Q2-Class

IXFK30N100Q2

IXFX30N100Q2

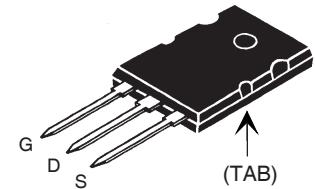
N-Channel Enhancement Mode
 Avalanche Rated, High dv/dt, Low Q_g
 Low intrinsic R_g, low t_{rr}



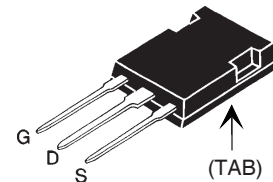
V_{DSS} = 1000V
I_{D25} = 30A
R_{DS(on)} ≤ 400mΩ
t_{rr} ≤ 300ns

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T _J = 25°C to 150°C	1000	V
V_{DGR}	T _J = 25°C to 150°C, R _{GS} = 1MΩ	1000	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	T _C = 25°C	30	A
I_{DM}	T _C = 25°C, pulse width limited by T _{JM}	120	A
I_A	T _C = 25°C	30	A
E_{AS}	T _C = 25°C	4	J
dv/dt	I _S ≤ I _{DM} , V _{DD} ≤ V _{DSS} , T _J ≤ 150°C	20	V/ns
P_D	T _C = 25°C	735	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6mm (0.062 in.) from case for 10s	300	°C
T_{SOLD}	Plastic body for 10s	260	°C
M_d	Mounting torque (IXFK)	1.13/10	Nm/lb.in.
F_C	Mounting force (IXFX)	20..120 /4.5..27	N/lb.
Weight	TO-264	10	g
	PLUS247	6	g

TO-264 (IXFK)



PLUS247 (IXFX)



G = Gate D = Drain
 S = Source TAB = Drain

Features

- Double metal process for low gate resistance
- International standard packages
- Epoxy meet UL 94 V-0, flammability classification
- Avalanche energy and current rated
- Fast intrinsic Rectifier

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values		
		(T _J = 25°C unless otherwise specified)		
		Min.	Typ.	Max.
BV_{DSS}	V _{GS} = 0V, I _D = 3mA	1000		V
V_{GS(th)}	V _{DS} = V _{GS} , I _D = 8mA	3.0		5.5 V
I_{GSS}	V _{GS} = ± 30V, V _{DS} = 0V			± 200 nA
I_{DSS}	V _{DS} = V _{DSS} V _{GS} = 0V			50 μA 2 mA
R_{DS(on)}	V _{GS} = 10V, I _D = 0.5 • I _{D25} , Note 1			400 mΩ

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{V}, I_D = 0.5 \cdot I_{D25}$, Note 1	20	30	S
C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		9400	pF
C_{oss}			766	pF
C_{rss}			153	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\Omega$ (External)		22	ns
t_r			14	ns
$t_{d(off)}$			60	ns
t_f			10	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		186	nC
Q_{gs}			46	nC
Q_{gd}			82	nC
R_{thJC}			0.17	$^\circ\text{C/W}$
R_{thCS}		0.15		$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$ unless otherwise specified)		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			30 A
I_{SM}	Repetitive, pulse width limited by T_{JM}			120 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{V}$, Note 1			1.5 V
t_{rr}	$I_F = 25\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$			300 ns
Q_{RM}			1	μC
I_{RM}			10	A

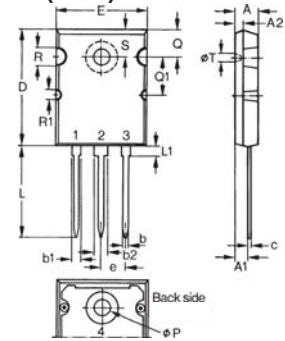
Note 1: Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

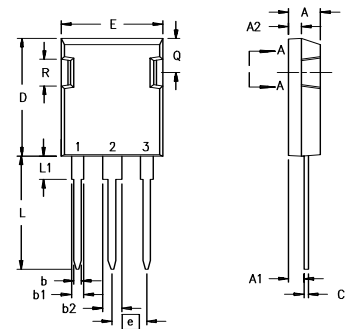
4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

TO-264 (IXFK) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

PLUS247™ (IXFX) Outline



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)
4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

Fig. 1. Output Characteristics
@ 25°C

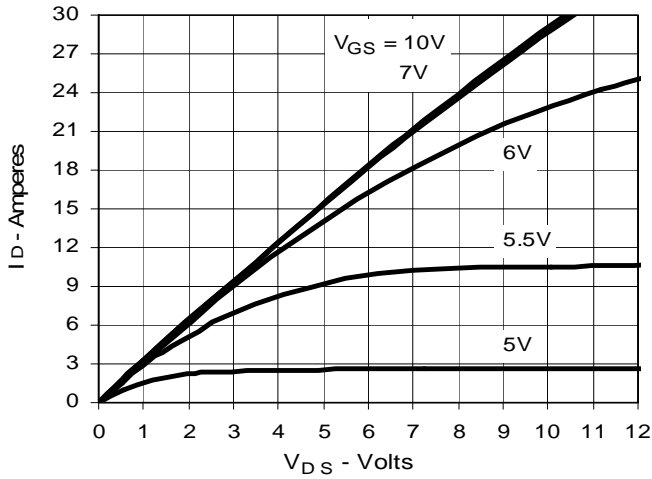


Fig. 2. Extended Output Characteristics
@ 25°C

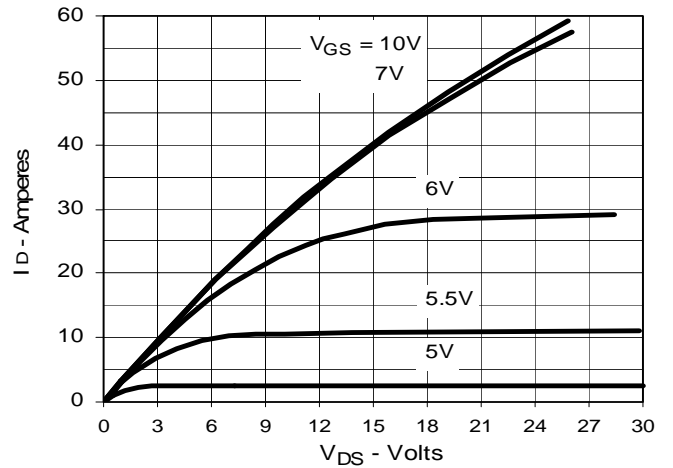


Fig. 3. Output Characteristics
@ 125°C

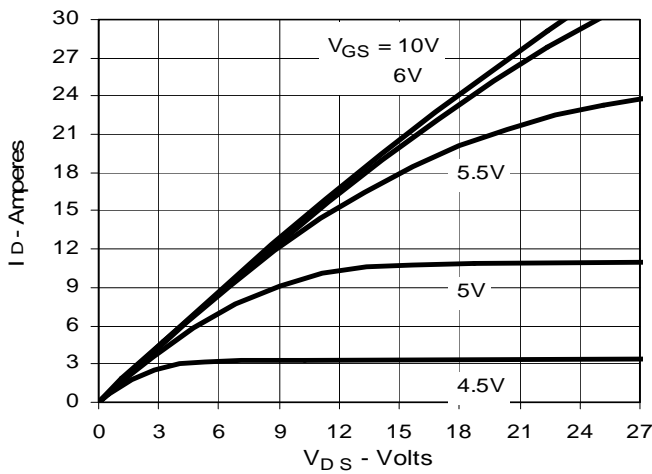


Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value
vs. Junction Temperature

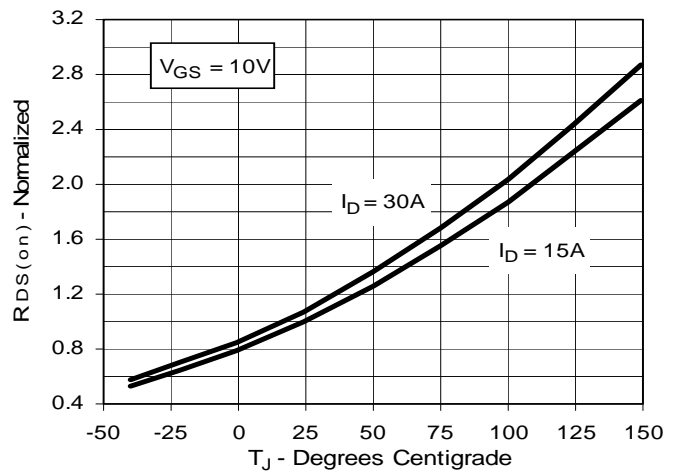


Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value
vs. I_D

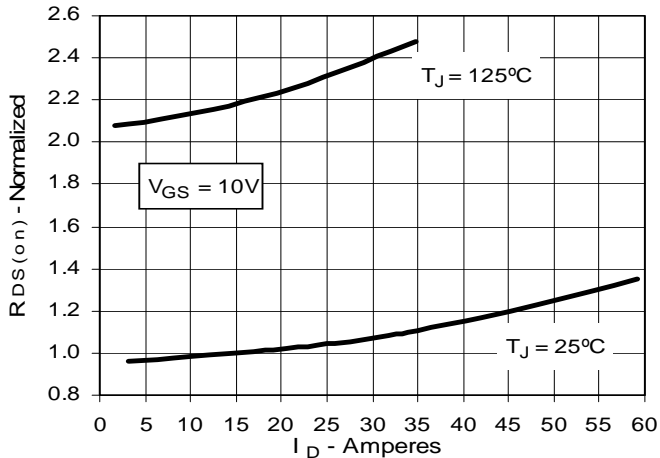


Fig. 6. Drain Current vs. Case Temperature

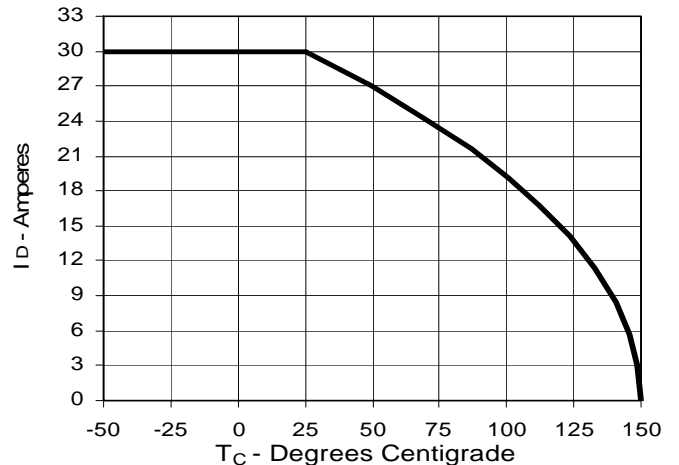


Fig. 7. Input Admittance

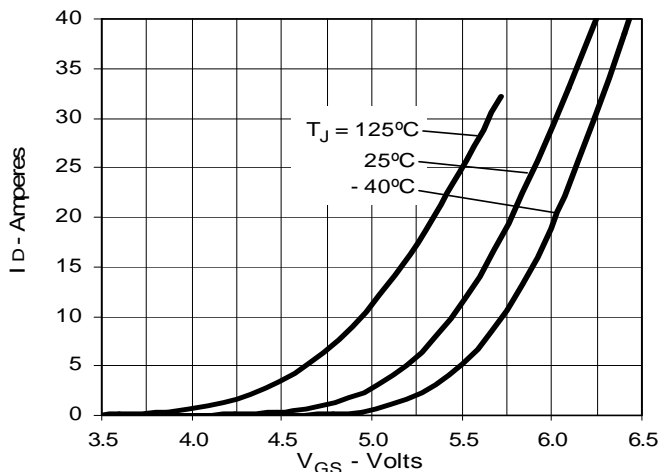


Fig. 8. Transconductance

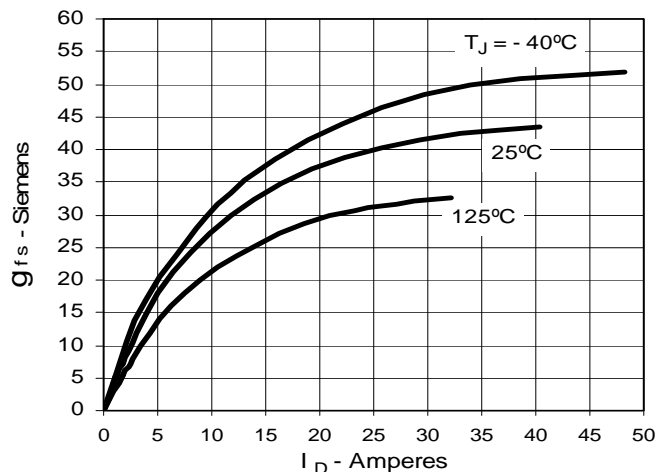


Fig. 9. Source Current vs. Source-To-Drain Voltage

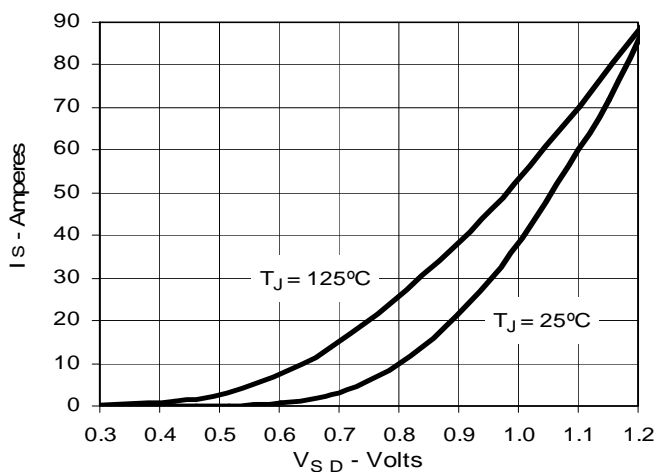


Fig. 10. Gate Charge

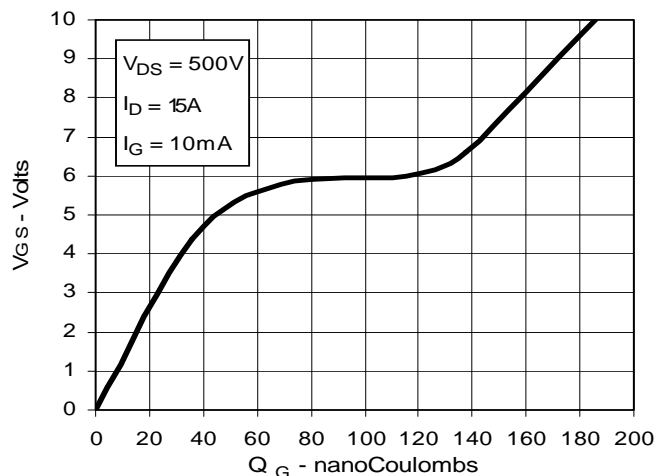


Fig. 11. Capacitance

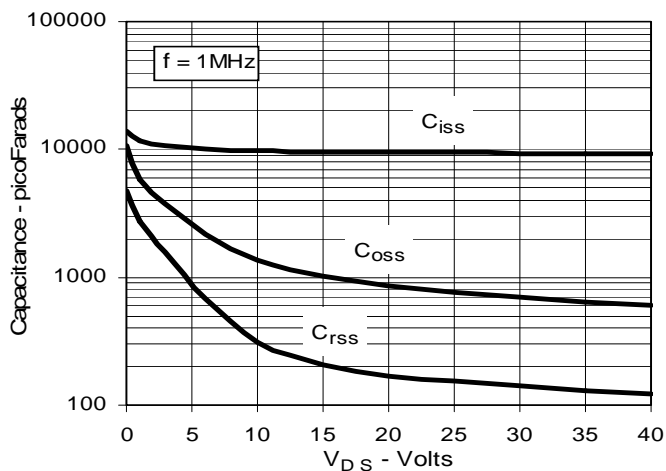


Fig. 12. Maximum Transient Thermal Impedance

